

Silicon NPN Power Transistors

2N6674 2N6675

DESCRIPTION

- With TO-3 package
- High voltage,high speed

APPLICATIONS

- Switching regulators
- Inverters
- Solenoid and relay drivers
- Deflection circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

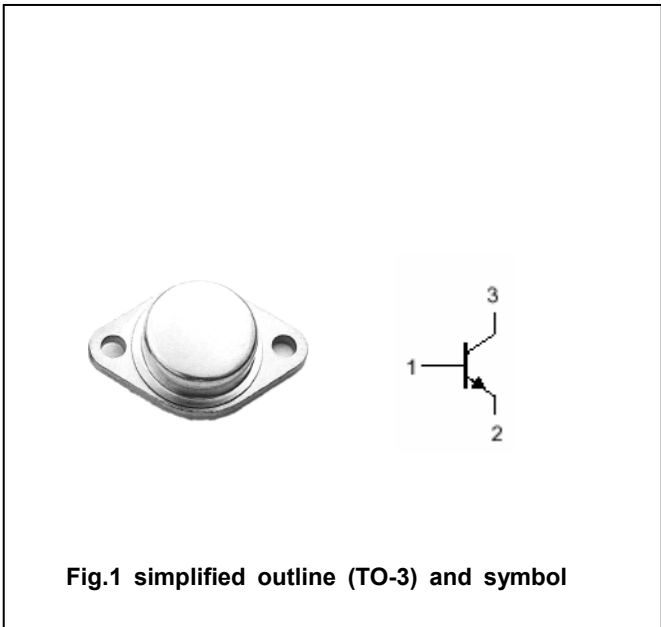


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6674	450	V
		2N6675	650	
V _{CEO}	Collector-emitter voltage	2N6674	300	V
		2N6675	400	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		15	A
I _B	Base current		5	A
P _T	Total Power Dissipation	T _a =25□	6	W
		T _C =25□	175	
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.0	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6674	I _C =0.2A ; I _B =0	300			V
		2N6675		400			
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =10A; I _B =2A			1.0	V	
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =15A; I _B =5A			5.0	V	
V _{BEsat}	Base-emitter saturation voltage	I _C =10A; I _B =2A			1.5	V	
I _{CBO}	Collector cut-off current	2N6674	V _{CB} =450V; I _E =0			0.1	mA
		2N6675		V _{CB} =650V; I _E =0			
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	mA	
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =3V	15		40		
h _{FE-2}	DC current gain	I _C =10A ; V _{CE} =2V	8		20		
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V;f=1MHz		15		MHz	

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)